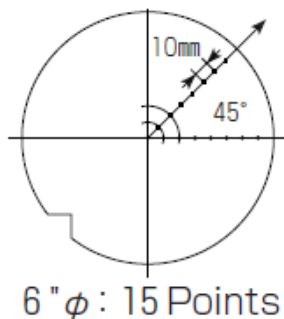


GaAs Single Crystal Wafers(Semi-Insulating Type)

Standard Specifications

Conduction Type	Semi-Insulating	
Growth Method·Dopant	VB·C-Controlled	
Use	For Epi.	
Carbon Concentration(cm ⁻³)	Controlled (0.5~20×10 ¹⁵)	
Carrier Concentration(cm ⁻³)	≤1×10 ⁸	
Resistivity(Ω·cm)	≥8×10 ⁷	
Mobility(cm ² /V·sec)	≥3000	
EPD Average(cm ⁻²)	≤10000	
Measuring Points of EPD	Fig.1	
Diameter(mm)	150±0.3	
Notch	SEMI Standards	
Edge Rounding(mmR)	0.25(Conform to SEMI Standards)	
Thickness(μm)	675±25	550±25
Orientation	(100)±0.3°, (100)2°off<110>±0.3°	
Surface Finish	P/P	
Surface Clean	SC+(Super Clean Plus)	
Flatness·LPD(*1)	Refer to other specification	
Package	Cassette	

Fig.1



Notes

(*1)LPD : Light Point Defects

Attached Data

- Standard : Resistivity, Mobility, Diameter, OF, IF, Thickness, Flatness(min.~max.)
- Option : EPD Map, Accuracy of Orientation, Light Point Defects